

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5149

HORIZONTAL DEFLECTION OUTPUT FOR MEDIUM RESOLUTION DISPLAY, COLOR TV

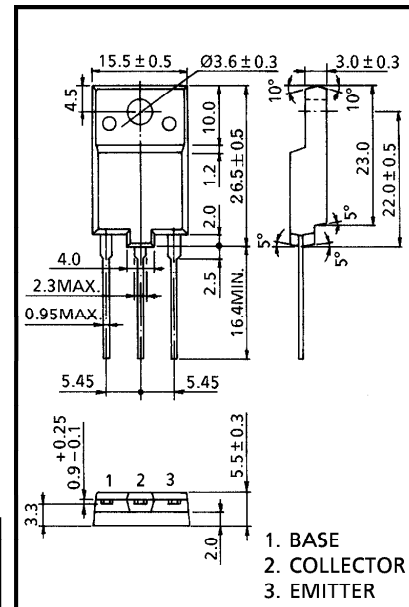
HIGH SPEED SWITCHING APPLICATIONS

- High Speed : $t_f = 0.2 \mu s$ (Typ.)
- High Voltage : $V_{CBO} = 1500V$
- Low Saturation Voltage : $V_{CE(sat)} = 5V$ (Max.)
- Built-in Damper Type
- Collector Metal (Fin) is Fully Covered with Mold Resin.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	1500	V
Collector-Emitter Voltage		V_{CEO}	600	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	8	A
	Pulse	I_{CP}	16	
Base Current		I_B	4	A
Collector Power Dissipation ($T_c = 25^\circ C$)		P_C	50	W
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$

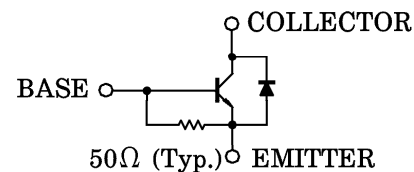
Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	2-16E3A

Weight : 5.5g (Typ.)

EQUIVALENT CIRCUIT



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● The information contained herein is subject to change without notice.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 1500V, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5V, I_C = 0$	66	—	200	mA
Emitter-Base Breakdown Voltage		V_{EBO}	$I_E = 400mA, I_C = 0$	5	—	—	V
DC Current Gain		$h_{FE} (1)$	$V_{CE} = 5V, I_C = 1A$	8	—	25	
		$h_{FE} (2)$	$V_{CE} = 5V, I_C = 5A$	3.8	—	8.0	
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 5A, I_B = 1.3A$	—	—	5	V
Base-Emitter Saturation Voltage		$V_{BE} (sat)$	$I_C = 5A, I_B = 1.3A$	—	1.0	1.3	V
Forward Voltage (Damper Diode)		$-V_F$	$I_F = 5A$	—	1.35	1.8	V
Transition Frequency		f_T	$V_{CE} = 10V, I_C = 0.1A$	—	2	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	110	—	pF
Switching Time	Storage Time	t_{stg}	$I_{CP} = 5A, I_{B1} (end) = 1.1A, f_H = 31.5kHz$	—	4	6	μs
	Fall Time	t_f		—	0.2	0.5	

